

AMENDMENTS TO THE TITLE:

As suggested, please replace the title with the following:

METHOD FOR FORMING CONTACT BUMPS FOR CIRCUIT BOARD

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AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph beginning at page 6, line 3, as follows:

An electrode pad 6 of Al, Au or so with a size of, for example, $10\ \mu\text{m} \times 10\ \mu\text{m}$ ~~should have been~~ is formed on a semiconductor chip 5. After the plated resist 3 is separated from the high-concentration impurity Si template 1, the electrode pad 6 on the semiconductor chip 5, as a wired board, is aligned with the Au-plated buried layer 4 and is bonded together by thermo-compression bonding or the like, as shown in Fig. 2C. At this time, applying vibration energy such as ultrasonic waves or so ensures more effective bonding of the electrode pad 6 and the Au-plated buried layer 4.

Please amend the paragraph beginning at page 12, line 8, as follows:

First, an Si substrate having an impurity injected therein at a high concentration of, for example, ~~$1 \times 10^{17}\text{-cm}^{-3}$~~ $1 \times 10^{17}\text{ cm}^{-3}$ or higher to have a low electric resistance of ~~$1 \times 10^{-1}\ \Omega\text{-cm}$~~ $1 \times 10^{-1}\ \Omega\text{-cm}$ or lower is used as the high-concentration impurity Si template 1, as shown in Fig. 7A.